

SOT89 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

FCX558

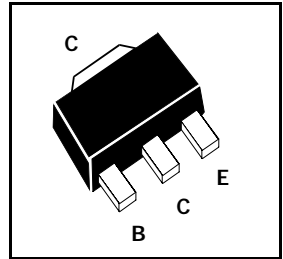
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FEATURES

- * 400 Volt V_{CEO}
- * P_{tot} = 1 Watt

COMPLEMENTARY TYPE – FCX458

PARTMARKING DETAIL – P58



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-200	mA
Peak Pulse Current	I_{CM}	-500	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-400		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-400		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}, I_{CES}		-100	nA	$V_{CB} = -320\text{V}; V_{CES} = 320\text{V}$
Emitter Cut-Off Current	I_{EBO}		-100	nA	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.2 -0.5	V	$I_C = -20\text{mA}, I_B = -2\text{mA}^*$ $I_C = -50\text{mA}, I_B = -6\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	$I_C = -50\text{mA}, I_B = -5\text{mA}^*$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		-0.9	V	$I_C = -50\text{mA}, V_{CE} = -10\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 15	300		$I_C = -1\text{mA}, V_{CE} = -10\text{V}$ $I_C = -50\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -100\text{mA}, V_{CE} = -10\text{V}^*$
Transition Frequency	f_T	50		MHz	$I_C = -10\text{mA}, V_{CE} = -20\text{V}$ $f = 20\text{MHz}$
Collector-Base Breakdown Voltage	C_{obo}		5	pF	$V_{CB} = -20\text{V}, f = 1\text{MHz}$
Switching times	t_{on} t_{off}		95 Typical 1600 Typical	ns ns	$I_C = -50\text{mA}, V_C = -100\text{V}$ $I_{B1} = -5\text{mA}, I_{B2} = -10\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device
For typical characteristics graphs see FZT558 datasheet.